

Amendments to the Specification:

Amend the paragraph starting on page 10, line 34 of the originally filed specification as follows.

The next step involves introducing dopant into the dielectric layer DS with the aid of an implantation mask R (Fig. 5) (~~not illustrated in the figure~~). The photoresist mask which remained above the emitter and with the aid of which the emitter E has already been patterned is preferably used for this purpose. The method thus becomes self-aligning relative to the structure of the emitter. Otherwise, an implantation mask R is used or produced which has openings S at the locations into which the dopant is subsequently to be introduced (indicated by the arrows I).